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**INFORMATION DISCLOSURE STATEMENT  
 IN A PATENT**  
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Applicants:  
 Osamu Goto, et al.

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### U.S. PATENT DOCUMENTS

Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If appropriate
ON	AA	6,060,335	5-9-00	Rennie			
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						

### FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
ON	AH	JP11-54794	2-26-99	Japan			Abstract	
ON	AI	JP09-266326	10-7-97	Japan			Abstract	
ON	AJ	JP11-243251	9-7-99	Japan			Abstract	
ON	AK	EP 0 803 916	10-29-99	Europe				
	AL							
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### OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

ON	AT	Shuji Nakamura, et al., "Characteristics of InGaN multi-quantum-well-structure laser diodes", Applied Physics Letters, 1996, Vol. 68, No. 23, pp. 3269-3271					
	AU						
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ON

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**\*EXAMINER:** Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.